

Model Comparison

Model	VRRMVDRM(V)	ITAVIFAV(A)
C1PDB52N08	800	60
C1PDB52N12	1200	60
C1PDB52N14	1400	60
C1PDB52N16	1600	60
C1PDB52N18	1800	60

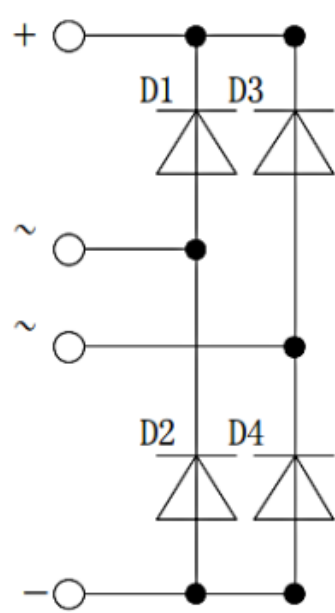
Features / Advantages

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop

Applications

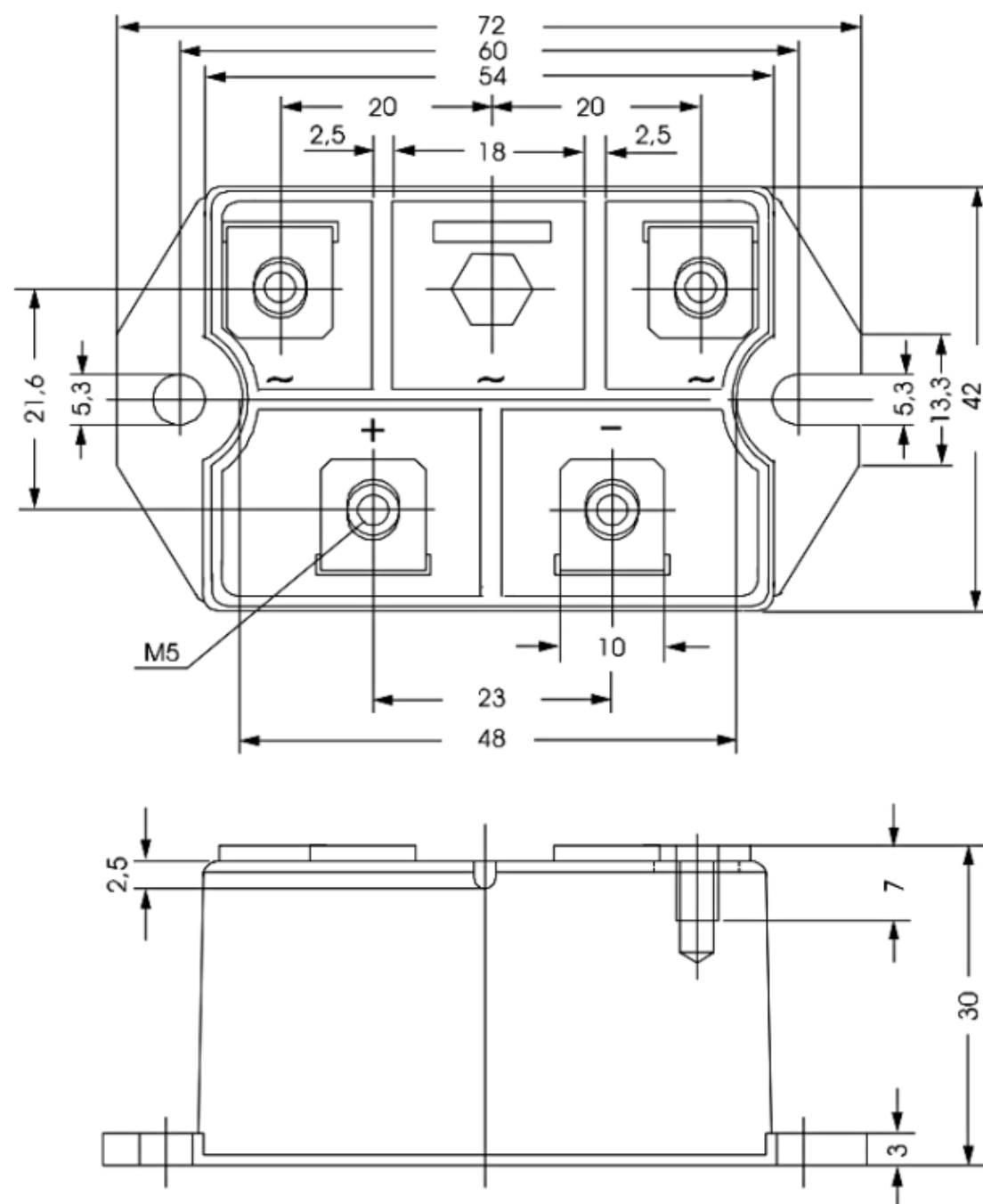
- Diode for main rectification
- For one phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Internal Circuit



Package Dimension

Dimensions in Millimeters



Parameters

Parametrics	C1PDB52N08~18
V_{RRM}	800~1800V
I_{dAV} @TC	60A
T_C	115°C
I_{FSM} 10ms, 45°C	550A
$V_{(FO)}$ @Tvj max	0.78V
Package style Outline drawings	XEA